Elektronische Bauelemente

SSD45N03

45A, 25V, $R_{DS(ON)}$ 9mΩ

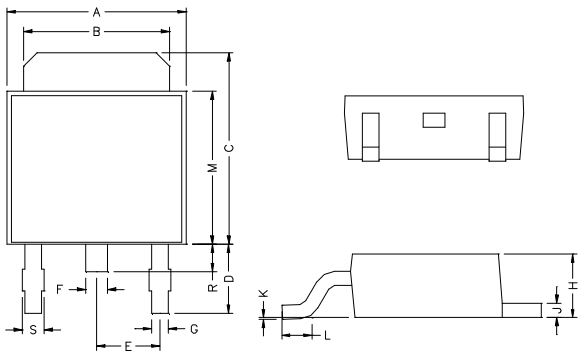
N-Channel Enhancement Mode Power Mos.FET

Description

The SSD45N03 provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

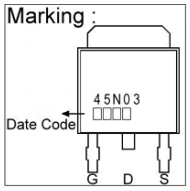
The TO-252 is universally preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

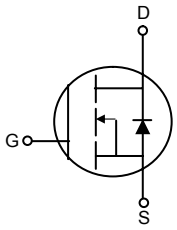
TO-252



Features

* RoHS Compliant
* Low Gate Charge
* Simple Drive Requirement
* Fast Switching Speed





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.40	6.80	G	0.50	0.70
B	5.20	5.50	H	2.20	2.40
C	6.80	7.20	J	0.45	0.55
D	2.20	2.80	K	0	0.15
E	2.30 REF.		L	0.90	1.50
F	0.70	0.90	M	5.40	5.80
S	0.60	0.90	R	0.80	1.20

Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	25	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current, V_{GS}@10V	I_D@T_C=25°C	45	A
Continuous Drain Current, V_{GS}@10V	I_D@T_C=100°C	32	A
Pulsed Drain Current[1]	I_{DM}	150	A
Total Power Dissipation	P_D@T_C=25°C	50	W
Linear Derating Factor		0.4	W/°C
Single Pulse Avalanche Energy[2]	E_{AS}	150	mJ
Avalanche Current	I_{AR}	25	A
Operating Junction and Storage Temperature Range	Tj, Tstg	-55~+150	°C

Thermal Data

Parameter		Symbol	Ratings	Unit
Thermal Resistance Junction-case	Max.	Rthj-c	2.5	°C/W
Thermal Resistance Junction-ambient	Max.	Rthj-a	110	°C/W

Electrical Characteristics(Tj=25°C Unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Drain-Source Breakdown Voltage	BV_{DSS}	25	–	–	V	V_{GS}=0V, I_D=250uA
Breakdown Voltage Temp. Coefficient	$\triangle BV_{DS}/\triangle Tj$	–	0.026	–	V/°C	Reference to 25°C, I_D=1mA
Gate Threshold Voltage	$V_{GS(th)}$	1.0	–	3.0	V	V_{DS}=V_{GS}, I_D=250uA
Gate-Source Leakage Current	I_{GSS}	–	–	±100	nA	V_{GS}=±20V
Drain-Source Leakage Current (Tj=25°C)	I_{DSS}	–	–	1	uA	V_{DS}=25V,V_{GS}=0
Drain-Source Leakage Current(Tj=150°C)		–	–	25	uA	V_{DS}=20V,V_{GS}=0
Static Drain-Source On-Resistance[3]	$R_{DS(ON)}$	–	6	9	mΩ	V_{GS}=10V, I_D=30A
		–	10	13		V_{GS}=4.5V, I_D=30A
Total Gate Charge[3]	Qg	–	15	–	nC	I_D=20A V_{DS}=20V V_{GS}= 4.5V
Gate-Source Charge	Qgs	–	4	–		
Gate-Drain ("Miller") Charge	Qgd	–	6	–		
Turn-on Delay Time[3]	$Td_{(ON)}$	–	8.8	–	nS	V_{DD}=15V I_D=20A V_{GS}=10V R_G=3.3Ω R_D=0.75Ω
Rise Time	Tr	–	57.5	–		
Turn-off Delay Time	$Td_{(Off)}$	–	18.5	–		
Fall Time	T_f	–	6.4	–		
Input Capacitance	Ciss	–	1135	–	pF	V_{GS}=0V V_{DS}=25V f=1.0MHz
Output Capacitance	Coss	–	200	–		
Reverse Transfer Capacitance	Crss	–	135	–		
Forward Transconductance	Gfs	–	25	–	S	V_{DS}=10V, I_D=10A

Source-Drain Diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Forward On Voltage[3]	V_{SD}	–	–	1.5	V	I_S=20 A, V_{GS}=0V
Continuous Source Current(Body Diode)	I_S	–	–	50	A	V_D=V_G=0V,V_S=1.5 V

Notes: 1.Pulse width limited by safe operating area.

2.Staring Tj=25°C,V_{DD}=25V,L=0.1mH,R_G=25Ω ,I_{AS}=10A

3.Pulse width≦300us, dutycycle≦2%.

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Characteristics Curve

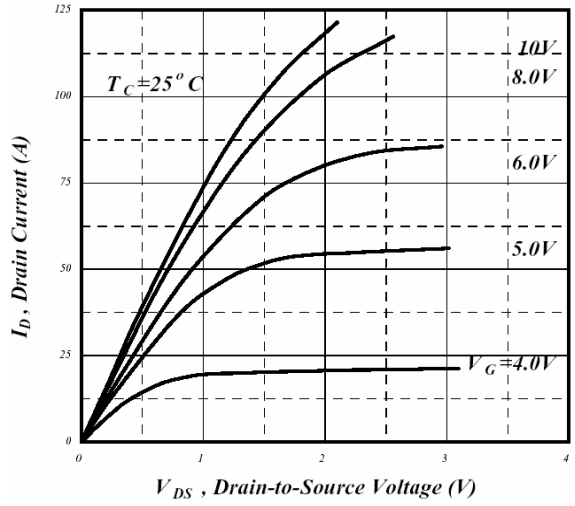

Fig 1. Typical Output Characteristics

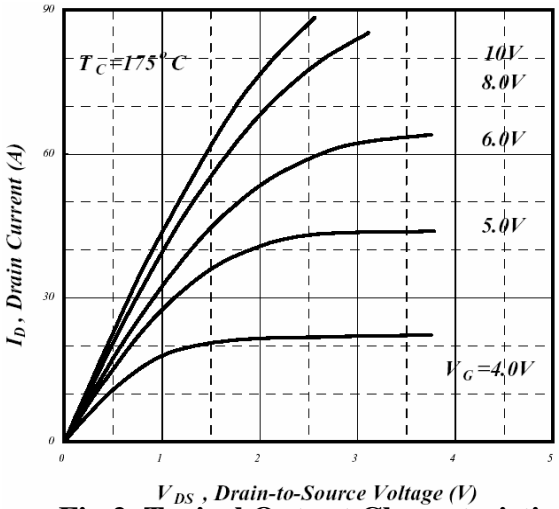

Fig 2. Typical Output Characteristics

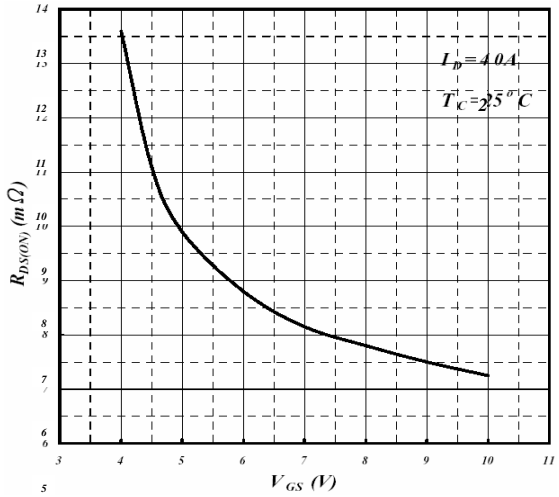

Fig 3. On-Resistance v.s. Gate Voltage

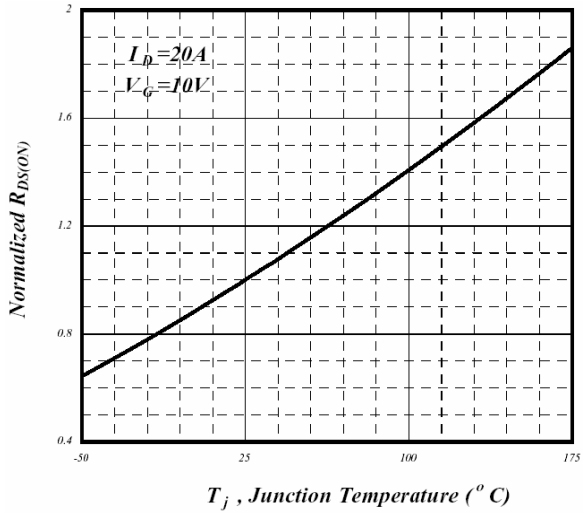

Fig 4. Normalized On-Resistance v.s. Junction Temperature

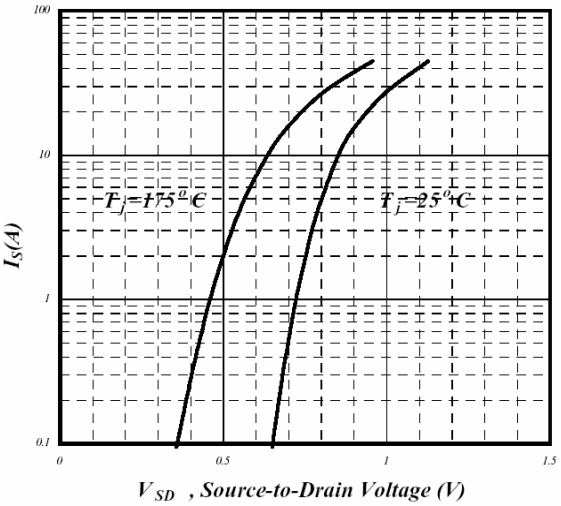

Fig 5. Forward Characteristics of Reverse Diode

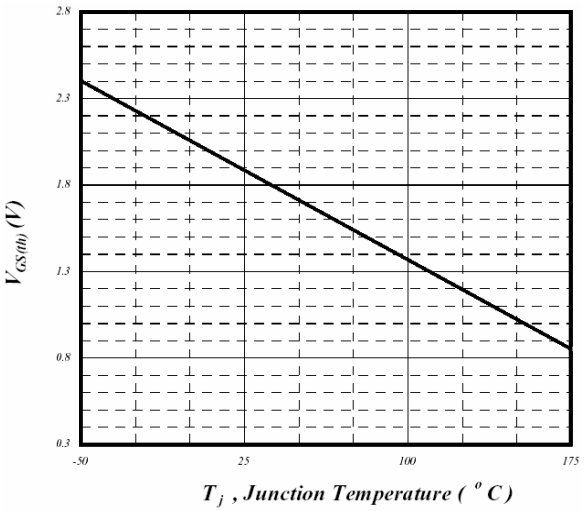

Fig 6. Gate Threshold Voltage v.s. Junction Temperature

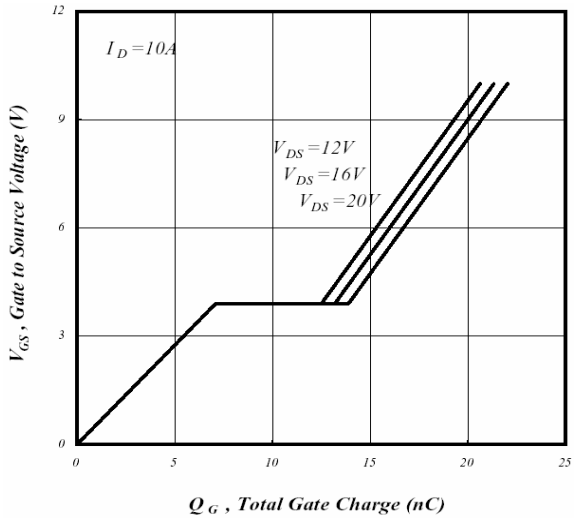

Fig 7. Gate Charge Characteristics

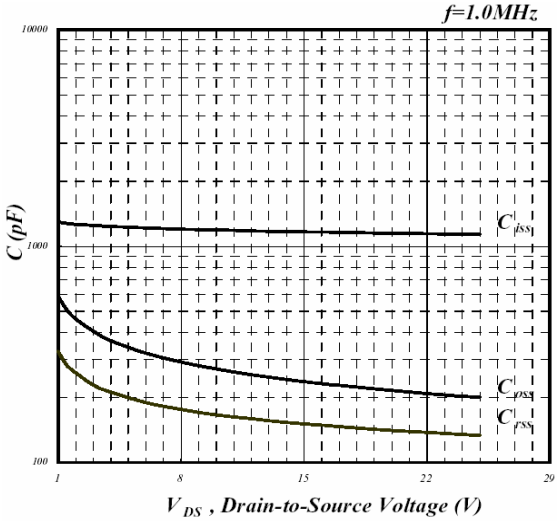

Fig 8. Typical Capacitance Characteristics

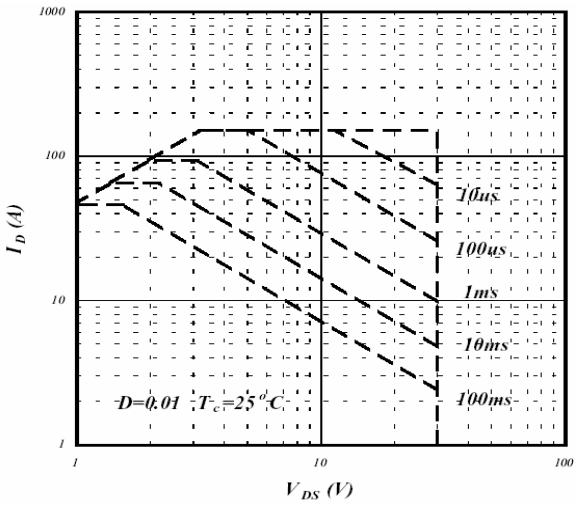

Fig 9. Maximum Safe Operating Area

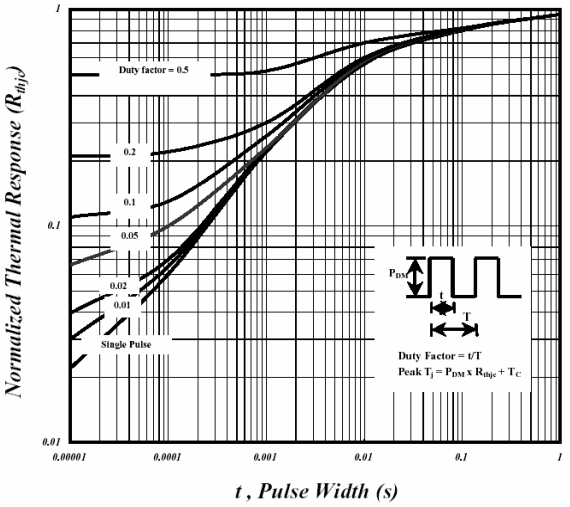

Fig 10. Effective Transient Thermal Impedance

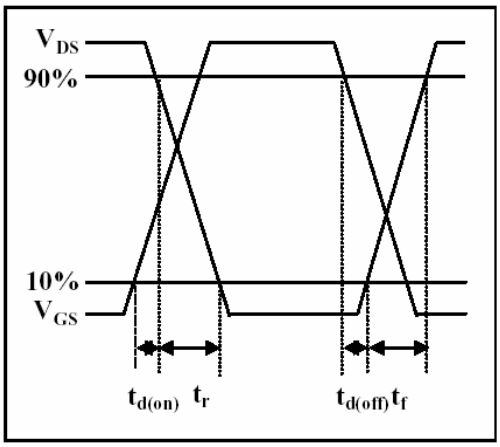

Fig 11. Switching Time Waveform

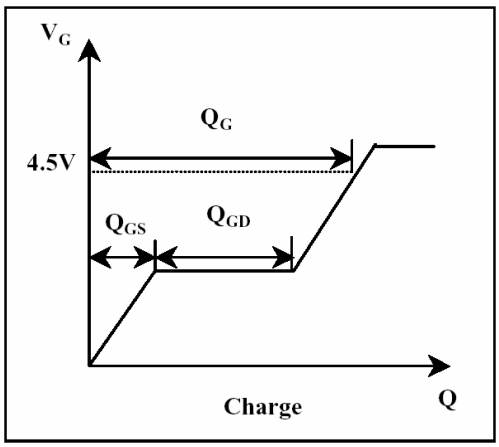

Fig 12. Gate Charge Waveform